

Technical Data Data Sheet N1176, Rev. - Green Products

186NQ200-1 SCHOTTKY RECTIFIER

Applications:

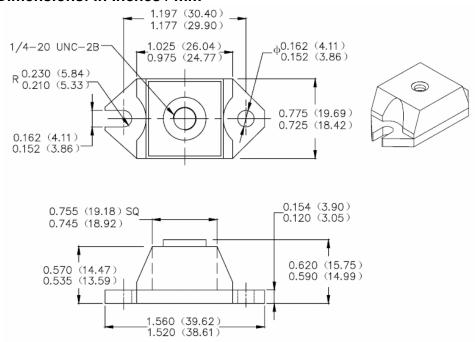
Switching power supply ● Converters ● Free-Wheeling diodes ● Reverse battery protection

Features:

- 175℃ T_J operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5'S
- Easier to mount and lower profile than DO-5'S
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

ANODE CATHODE

Mechanical Dimensions: In Inches / mm



PRM1-1(HALF PAK Module)

MARKING, MOLDING RESIN

Marking for 186NQ200-1, 1st row SS YYWWL, 2nd row 186NQ200-1 Where YY is the manufacture year WW is the manufacture week code L is the wafer's Lot Number Molding resin

Epoxy resin UL:94V-0

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Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Max. Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =110°C, rectangular wave form	180	А
Max. Peak One Cycle Non- Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	3000	Α

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	V_{F1}	@ 180A, Pulse, T _J = 25 °C	1.12	V
	V_{F2}	@ 180A, Pulse, T _J = 125 °C	0.79	V
Max. Reverse Current (per	I _{R1}	$@V_R = \text{rated } V_R T_J = 25 ^{\circ}\text{C}$	4.5	mA
leg) *	I _{R2}	$@V_R = \text{rated } V_R T_J = 125 ^{\circ}\text{C}$	65	mA
Max. Junction Capacitance (per leg)	C _T	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	2700	pF
Typical Series Inductance (per leg)	L _S	Measured lead to lead 5 mm from package body	6.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/μs

Pulse Width < 300µs, Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification		Units	
Max. Junction Temperature	TJ	-	-55 to +175		°C	
Max. Storage Temperature	T _{stg}	-	-55 to +175		°C	
Maximum Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.30		°C/W	
Typical Thermal Resistance, case to Heat Sink	$R_{\theta cs}$	Mounting surface, smooth and greased	0.15		°C/W	
Mounting Torque	Тм	Non-lubricated threads	Mounting Torque	23(min) 29(max)	- Kg-cm	
			Terminal Torque	35(min) 46(max)		
Approximate Weight	wt	-	25.6		g	
Case Style	PRM1-1					

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Typical Forward Characteristics 10² 200°C 175°C 10¹ 10¹ 10¹ 10⁻¹ 10⁻¹ 0.0 0.2 0.4 0.6 0.8 1.0

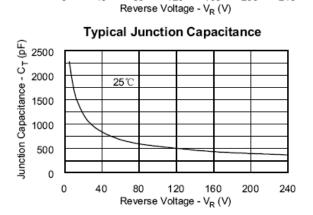
Forward Voltage Drop - VF (V)

10² 200°C 175°C 175°C 100°C 100°C

25 ℃

120

Typical Reverse Characteristics



10⁻³

0

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